

N-channel 30 V 11.6 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 3 — 24 October 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	37	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	29	W
Tj	junction temperature		-55	-	175	°C
Static char	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	12.3	14.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	9.9	11.6	mΩ
Dynamic c	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; \text{see}$ Figure 14; see Figure 15	-	1.4	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; \text{see}$ Figure 14; see Figure 15	-	4.9	-	nC



SOT669 (LFPAK; Power-SO8)

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		2
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

3. Ordering information

Table 3. Ordering information

Type number	Package	Package							
	Name	Description	Version						
PSMN011-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669						

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	37	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	26	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 4	-	150	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	29	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	140	-	V
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	-	26	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	150	Α
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 37 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω; unclamped; see <u>Figure 3</u>	-	9	mJ

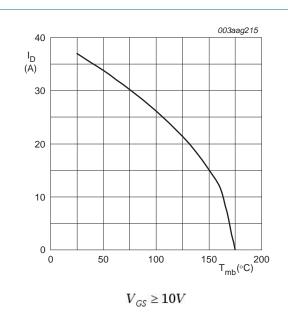


Fig 1. Continuous drain current as a function of mounting base temperature

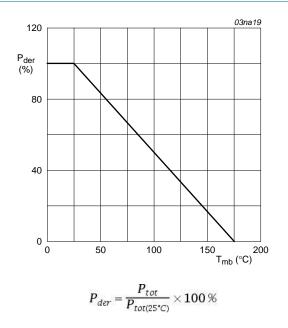
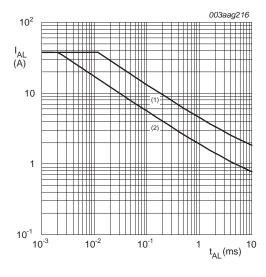


Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j (init)} = 25^{\circ}C$; (2) $T_{j (init)} = 100^{\circ}C$

Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

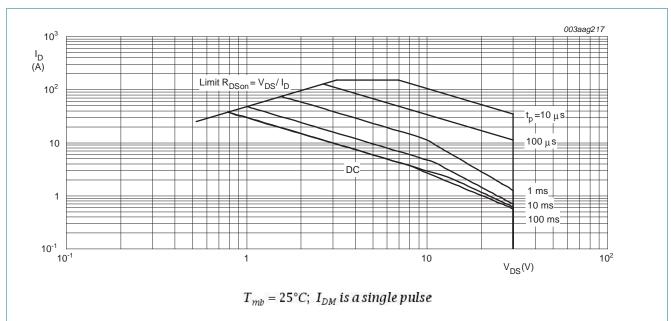


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 5	-	4.87	5.06	K/W

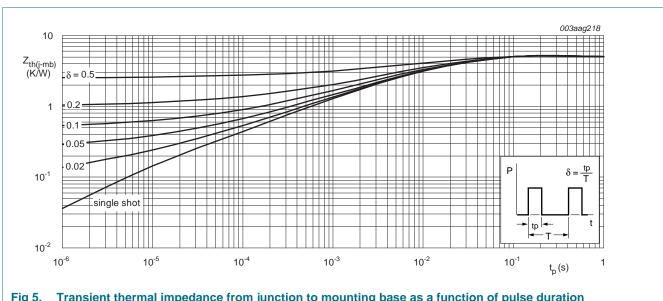


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.57	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	12.3	14.5	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	23.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	9.9	11.6	mΩ
		$V_{GS} = 10 \text{ V}$; $I_D = 10 \text{ A}$; $T_j = 150 \text{ °C}$; see Figure 12; see Figure 13	-	-	18.8	mΩ
R_{G}	gate resistance	f = 1 MHz	-	2	4	Ω
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 10 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	10.3	-	nC
		$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	9	-	nC
Q_{GS}	gate-source charge	$I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	1.5	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	1.1	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.4	-	nC
Q_{GD}	gate-drain charge		-	1.4	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 10 \text{ A}$; $V_{DS} = 15 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.5	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	641	-	pF
C _{oss}	output capacitance	$T_j = 25$ °C; see Figure 16	-	146	-	pF
C _{rss}	reverse transfer capacitance		-	46	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$	-	13.4	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	12.7	-	ns
t _{d(off)}	turn-off delay time		-	16.8	-	ns
t _f	fall time		-	6.6	-	ns

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 Table 6.
 Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}; $ $T_j = 25 \text{ °C}$	-	3.8	-	nC
Source-drain	diode					
V _{SD}	source-drain voltage	$I_S = 10 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.85	1.1	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A}/\mu s;$	-	17	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	7	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 10 \text{ A};$	-	10	-	ns
t _b	reverse recovery fall time	$dI_S/dt = -100 A/\mu s$; $V_{DS} = 15 V$; see Figure 18	-	7	-	ns

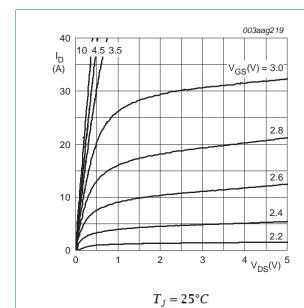


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

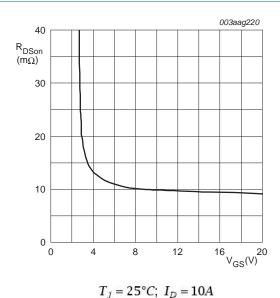
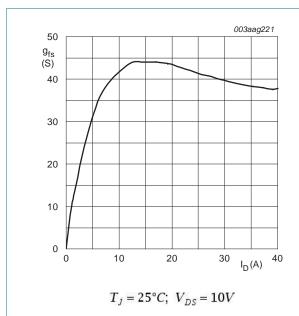
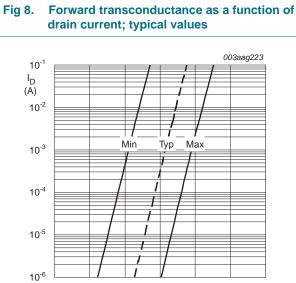


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



drain current; typical values



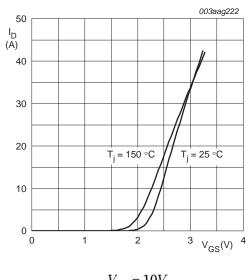
1

 $T_j = 25^{\circ}C; \ V_{DS} = 5V$

3

 $V_{GS}(V)$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



 $V_{DS} = 10V$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

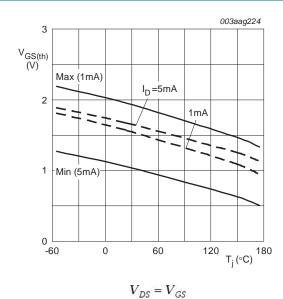


Fig 11. Gate-source threshold voltage as a function of junction temperature

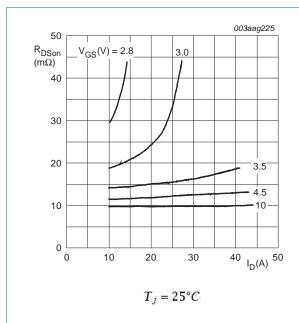


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

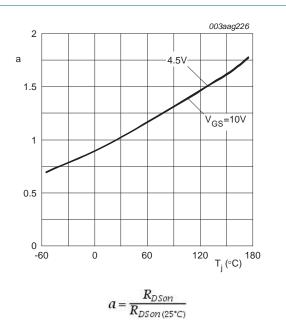


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

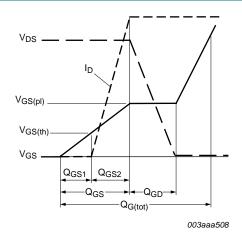
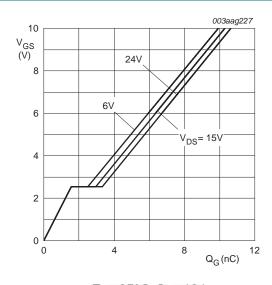


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 10A$

Fig 15. Gate-source voltage as a function of gate charge; typical values

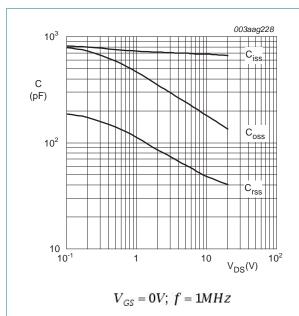


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

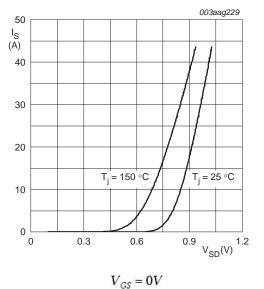


Fig 17. Source current as a function of source-drain voltage; typical values

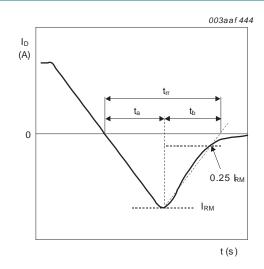
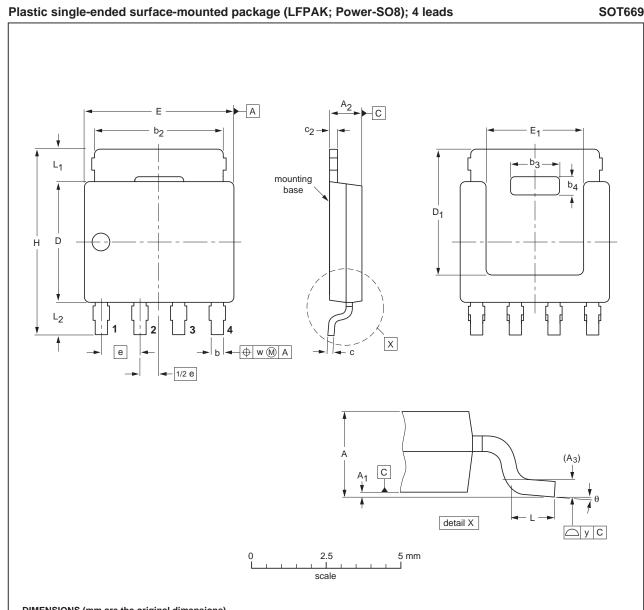


Fig 18. Reverse recovery timing definition

Package outline



DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	A ₂	A ₃	b	b ₂	b ₃	b ₄	С	c ₂	D ⁽¹⁾	D ₁ ⁽¹⁾ max	E ⁽¹⁾	E ₁ ⁽¹⁾	е	Н	L	L ₁	L ₂	w	у	θ
mm	1.20 1.01	0.15 0.00		0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7		0.30 0.24		4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT669		MO-235				06-03-16 11-03-25	

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN011-30YLC

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
PSMN011-30YLC v.3	20111024	Product data sheet	-	PSMN011-30YLC v.2				
Modifications:	Data sheet status changed from preliminary to product.							
	 Various changes to 	content.						
PSMN011-30YLC v.2	20110930	Preliminary data sheet	-	PSMN011-30YLC v.1				

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Nexperia

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